

WAFER PRODUCING METHOD

ABSTRACT OF THE DISCLOSURE

A wafer producing method for producing a wafer from an ingot, the ingot being previously formed with a separation layer along which the wafer is to be separated from the ingot. The wafer producing method includes a first ultrasonic vibration applying step of applying ultrasonic vibration to a given area of the ingot at a high density to thereby form a partially broken portion where a part of the separation layer is broken, a second ultrasonic vibration applying step of applying the ultrasonic vibration to the whole area of the ingot larger than the given area at a low density, after performing the first ultrasonic vibration applying step, thereby forming a fully broken portion where the separation layer is fully broken in such a manner that breaking starts from the partially broken portion, and a separating step of separating the wafer from the ingot along the fully broken portion.

[Fig. 5B]